

## Descriptions

This is 500V 13A N-Channel Enhancement Mode Power MOSFET in a TO-220/TO-220F package

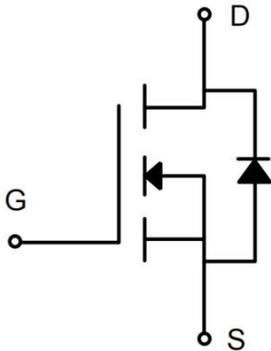
## Features

- Typ.RDS(on)=0.35Ω@VGS=10V
- 100% avalanche tested
- RoHS Compliant

## Applications

- SMPS
- Charger
- DC-DC

## Equivalent Circuit



## Pinning

TO-220



TO-220F



## Absolute Maximum Ratings (TC=25°C)

| Parameter                                   | Symbol              | CT13N50RA | CT13N50FA | Unit |
|---|---------------------|-----------|-----------|------|
| Drain-source voltage                        | V <sub>DSS</sub>    | 500       |           | V    |
| Gate-source voltage                         | V <sub>GS</sub>     | ±30       |           | V    |
| Continuous drain current                    | I <sub>D</sub>      | 13        |           | A    |
| Pulsed drain current <sup>1</sup>           | I <sub>DM</sub>     | 52        |           | A    |
| Avalanche energy, single pulse <sup>2</sup> | E <sub>AS</sub>     | 720       |           | mJ   |
| Power dissipation                           | P <sub>D</sub>      | 150       | 41        | W    |
| Derate above 25°C                           |                     | 1.2       | 0.33      | W/°C |
| Operating junction temperature              | T <sub>J</sub>      | -55~150   |           | °C   |
| Storage temperature                         | T <sub>stg</sub>    | -55~150   |           | °C   |
| Continuous diode forward current            | I <sub>S</sub>      | 13        |           | A    |
| Diode pulse current <sup>1</sup>            | I <sub>Spulse</sub> | 52        |           | A    |

## Thermal Characteristic

| Parameter                               | Symbol           | CT13N50RA | CT13N50FA | Unit |
|---|------------------|-----------|-----------|------|
| Thermal resistance, junction-to-case    | R <sub>θJC</sub> | 0.83      | 3         | °C/W |
| Thermal resistance, junction-to-ambient | R <sub>θJA</sub> | 62.5      | 62.5      | °C/W |

### Electrical Characteristics

| Parameter                           | Symbol  | Test Condition    | Test Condition | Min | Typ  | Max  | Unit |
|-------------------------------------|---------|-------------------|----------------|-----|------|------|------|
| Drain-source break down voltage     | BVDSS   | ID=250μA, VGS=0V  | TC=25°C        | 500 | -    | -    | V    |
| Gate threshold voltage              | VGS(th) | ID=250μA, VDS=VGS | TJ=25°C        | 2.0 | -    | 4.0  | V    |
| Drain-source leakage current        | DSS     | VDS=500V, VGS=0V  | TJ=25°C        | -   | -    | 1    | μA   |
| Gate-source leakage current,forward |         | VDS=400V, VGS=0V  | TJ=125°C       | -   | -    | 100  | μA   |
| Gate-source leakage current,forward | IGSSF   | VDS=0V, VGS=30V   | TJ=25°C        | -   | -    | 100  | nA   |
| Gate-source leakage current,reverse | IGSSR   | VDS=0V, VGS=-30V  | TJ=25°C        | -   | -    | -100 | nA   |
| Drain-source on-state resistance    | RDS(ON) | VGS=10V, ID=6.5A  | TJ=25°C        | -   | 0.35 | 0.48 | Ω    |

### Dynamic Characteristics of MOSFET (TC=25°C)

| Parameter                         | Symbol | Test Condition          | Min | Typ  | Max | Unit |
|-----------------------------------|--------|-------------------------|-----|------|-----|------|
| Input capacitance                 | Ciss   | f=1MHz, VDS=25V, VGS=0V | -   | 1978 | -   | pF   |
| Output capacitance                | Coss   |                         | -   | 185  | -   | pF   |
| Reverse transfer capacitance      | Crss   | VDD=120V                | -   | 9    | -   | pF   |
| Gate to source charge             | Qgs    | IB=13A                  | -   | 10   | -   | nC   |
| Gate to drain charge <sup>3</sup> | Qgd    | VGS= 0 to10V            | -   | 9    | -   | nC   |
| Total gate charge <sup>3</sup>    | Qg     |                         | -   | 34   | -   | nC   |

### Switching Characteristics of MOSFET (TC=25°C)

| Parameter           | Symbol | Test Condition                            | Min | Typ | Max | Unit |
|---------------------|--------|---|-----|-----|-----|------|
| Turn-on delay time  | td on  | VDS=250V, IB=13A,<br>RG=10Ω, VGS=0 to 10V | -   | 14  | -   | ns   |
| Rise time           | tr     |   | -   | 11  | -   | ns   |
| Turn-off delay time | td off |   | -   | 39  | -   | ns   |
| Fall time           | tf     |   | -   | 18  | -   | ns   |

### Characteristics of Body Diode (TC=25°C)

| Parameter                | Symbol | Test Condition                             | Min | Typ | Max | Unit |
|--------------------------|--------|--|-----|-----|-----|------|
| Forward voltage          | VSD    | ISD=13A, VGS=0V                            | -   | -   | 1.5 | V    |
| Reverse recovery time    | trr    | VDS=250V, IS=13A, VGS=0V<br>-di/dt=100A/μs | -   | 274 | -   | ns   |
| Reverse recovery current | Irr    |  | -   | 18  | -   | A    |
| Recovery charge          | Qrr    |  | -   | 2.5 | -   | μC   |

Notes:

1. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 150^{\circ}C$ .
2. The  $E_{AS}$  data shows Max. rating . The test condition is  $V_{DD} = 50V, V_{GS} = 10V, L = 10mH, I_{AS} = 12A, T_c = 25^{\circ}C$ .
3. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$ .

Electrical Characteristic Curve

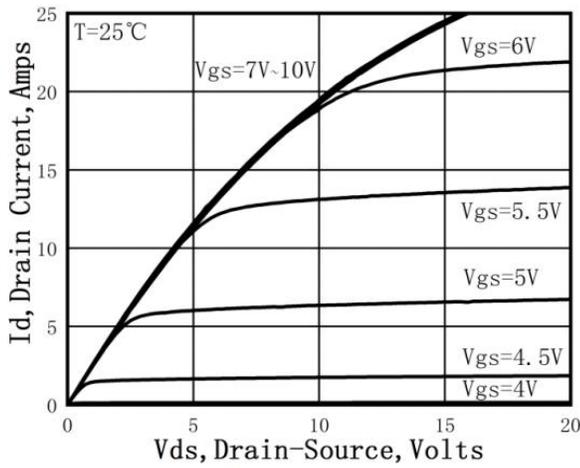


Figure 1. On-Region Characteristics

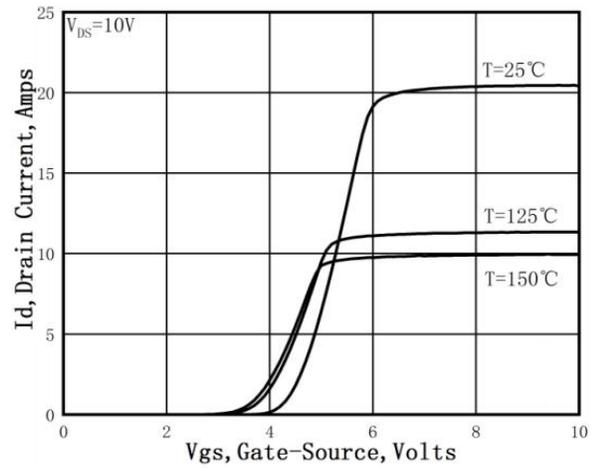


Figure 2. Transfer Characteristics

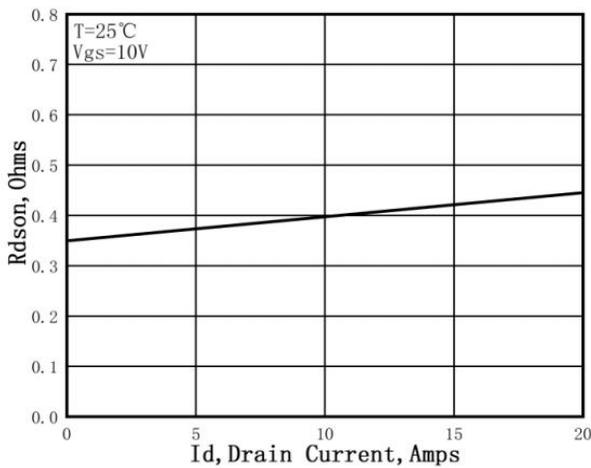


Figure 3. Static Drain-Source On Resistance

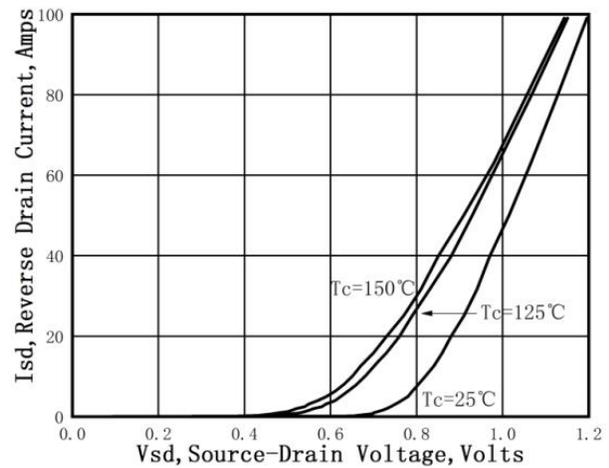


Figure 4. Typical Body Diode Transfer Characteristics

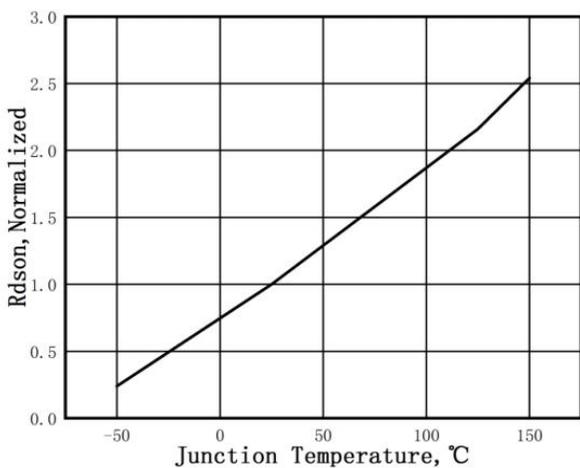


Figure 5. Normalized  $R_{DS(on)}$  vs. Temperature

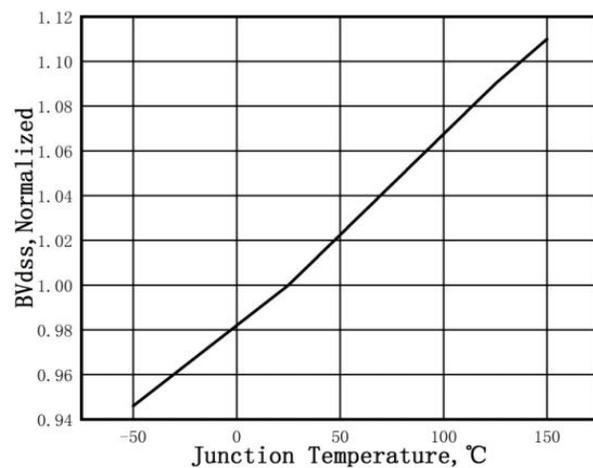


Figure 6. Normalized  $BV_{DSS}$  vs. Temperature

Electrical Characteristic Curve

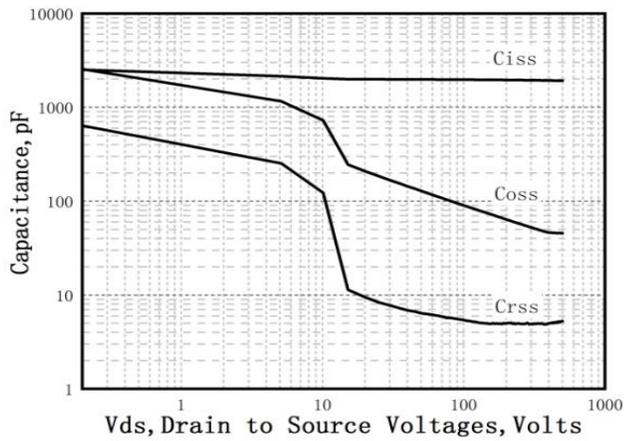


Figure 7. Capacitance Characteristics

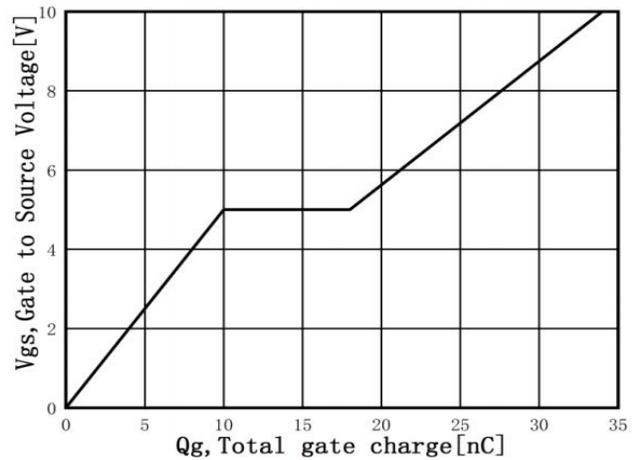


Figure 8. Gate Charge Characteristics

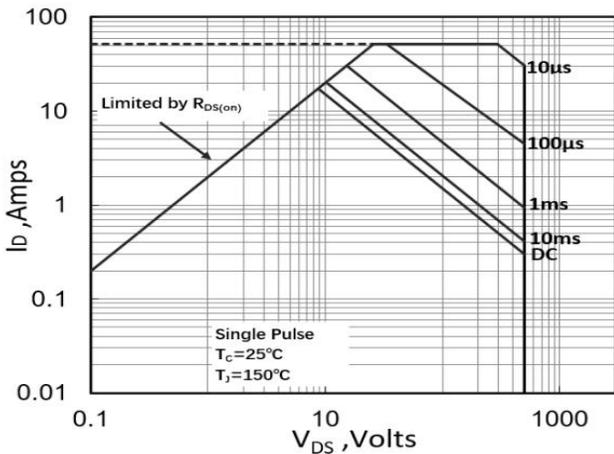


Figure 9. Maximum Safe Operating Area (TO-220)

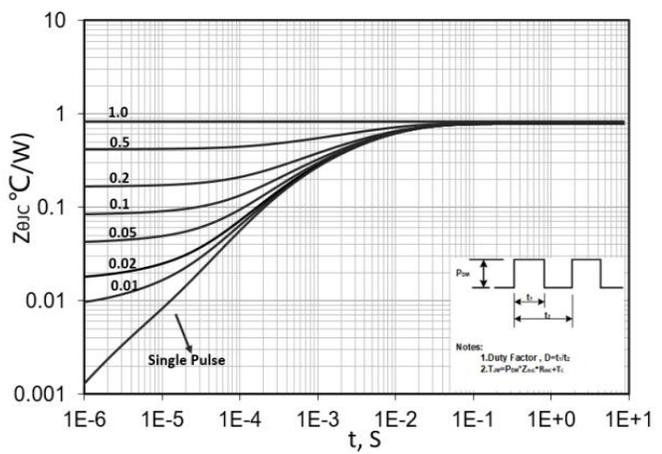


Figure 10. Transient Thermal Response Curve (TO-220)

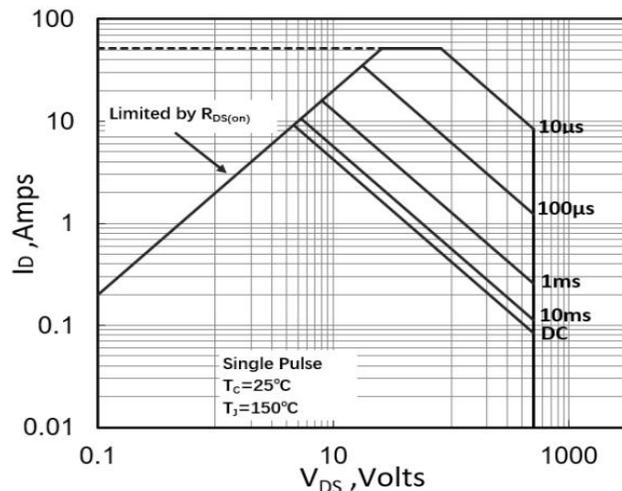


Figure 11. Maximum Safe Operating Area (TO-220F)

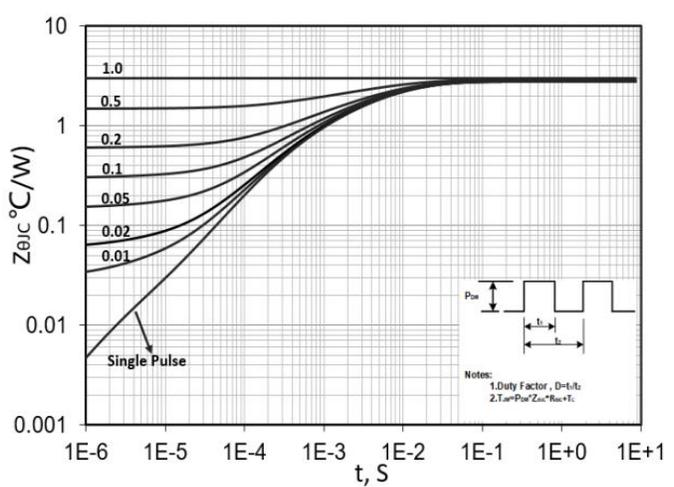
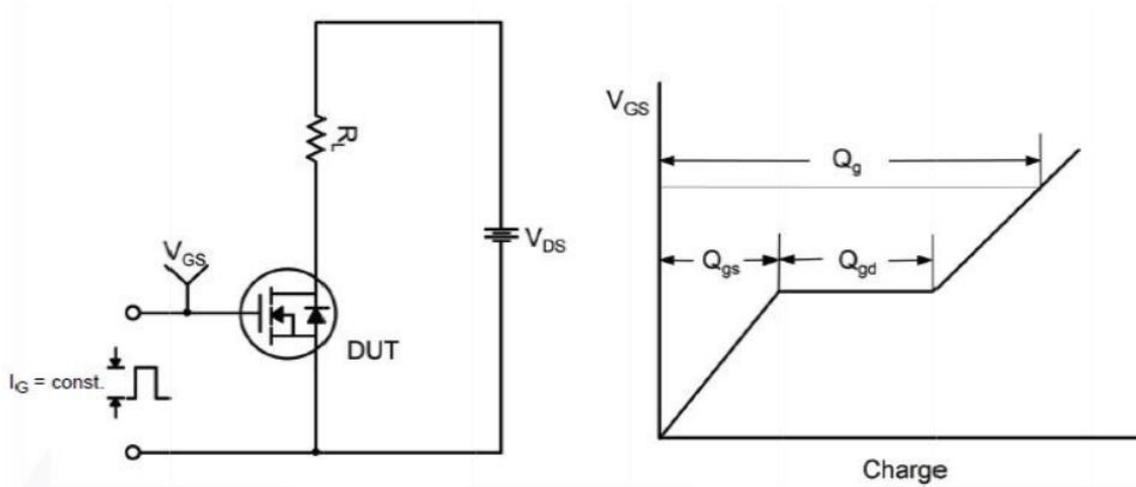


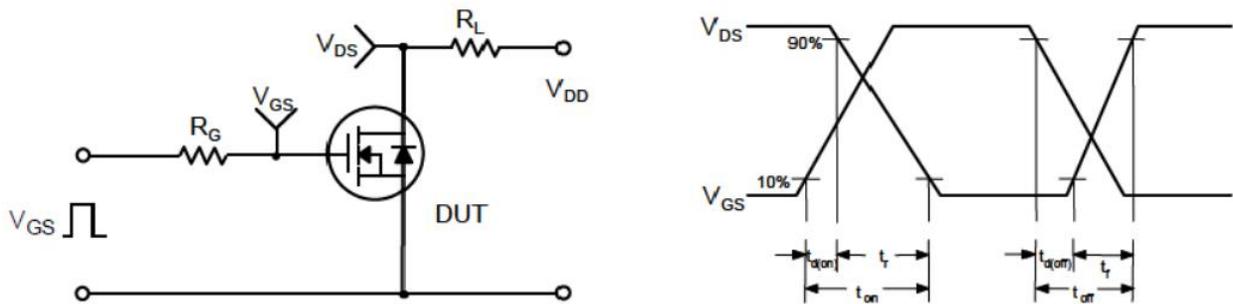
Figure 12. Transient Thermal Response Curve (TO-220F)

Test Circuit

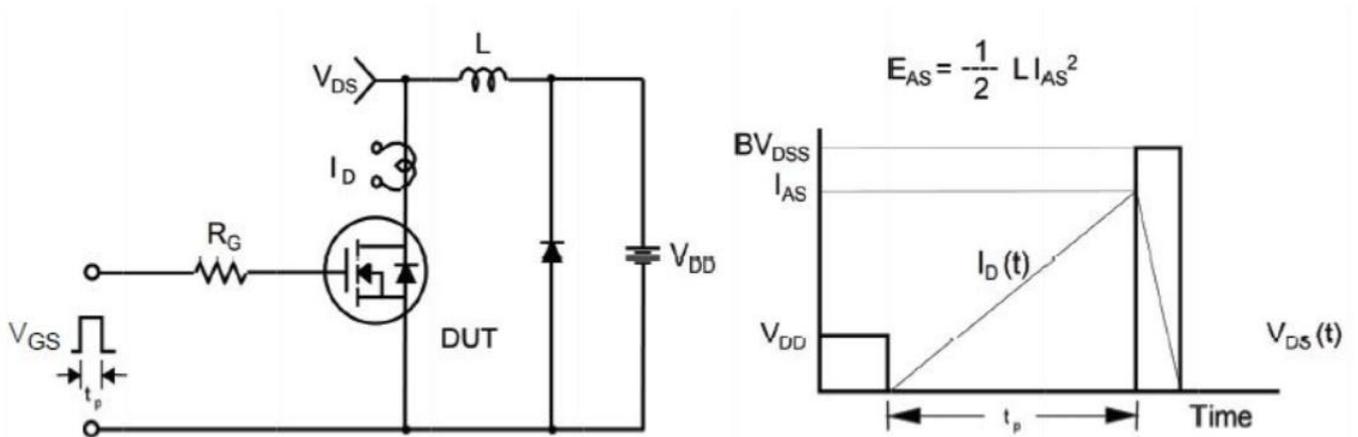
Gate Charge Test Circuit & Waveform



Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



**Marking Information**



Note:

COT: Company Code

13N50: Product Type.

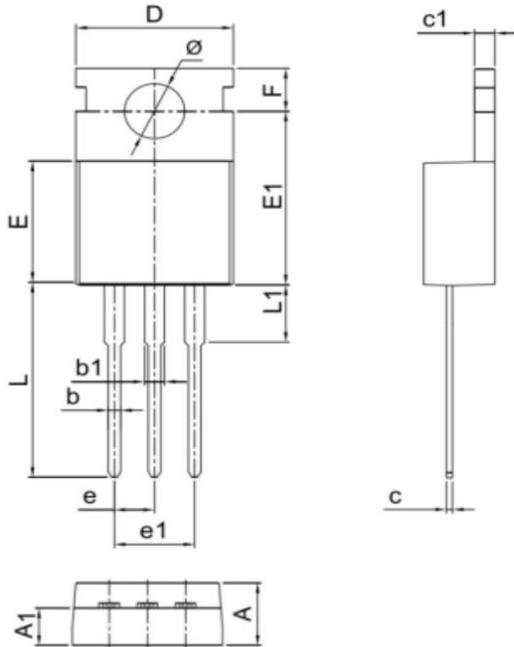
\*\*\*\*\*: \*: Inner Code \* : Year Code \*\*: Week Code \*\*: Lot Code.

**Ordering Information**

| Part      | Package | Marking | Packing method |
|-----------|---------|---------|----------------|
| CT13N50RA | TO-220  | 13N50   | Tube           |
| CT13N50FA | TO-220F | 13N50   | Tube           |

**Mechanical Dimensions**

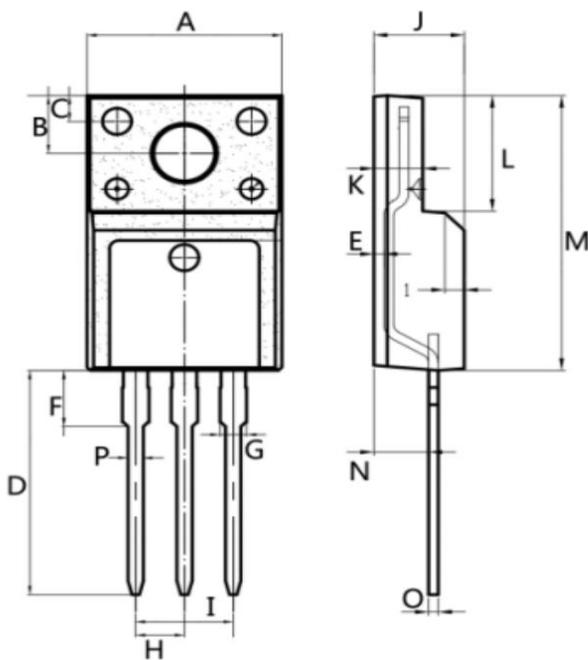
**Mechanical Dimensions for TO-220**



**COMMON DIMENSIONS**

| SYMBOL | MM    |       |
|--------|-------|-------|
|        | MIN   | MAX   |
| A      | 4.30  | 4.70  |
| A1     | 2.30  | 2.82  |
| b      | 0.70  | 0.94  |
| b1     | 1.17  | 1.41  |
| c      | 0.30  | 0.64  |
| c1     | 1.17  | 1.44  |
| D      | 9.70  | 10.20 |
| E      | 8.50  | 9.30  |
| E1     | 12.00 | 12.50 |
| e      | 2.44  | 2.64  |
| e1     | 4.88  | 5.26  |
| F      | 2.60  | 2.94  |
| L      | 13.00 | 14.00 |
| L1     | 3.385 | 4.20  |
| Ø      | 3.74  | 3.95  |

**Mechanical Dimensions for TO-220F**



**COMMON DIMENSIONS**

| SYMBOL | MM    |       |
|--------|-------|-------|
|        | MIN   | MAX   |
| A      | 9.95  | 10.36 |
| B      | 2.95  | 3.55  |
| C      | 1.25  | 1.6   |
| D      | 12.64 | 13.5  |
| E      | 0.40  | 0.60  |
| F      | 2.80  | 3.80  |
| G      | 1.14  | 1.58  |
| H      | 2.44  | 2.64  |
| I      | 4.88  | 5.26  |
| J      | 4.50  | 4.90  |
| K      | 2.34  | 2.80  |
| L      | 6.48  | 6.90  |
| M      | 15.40 | 16.07 |
| N      | 2.66  | 3.50  |
| O      | 0.40  | 0.64  |
| P      | 0.70  | 0.94  |